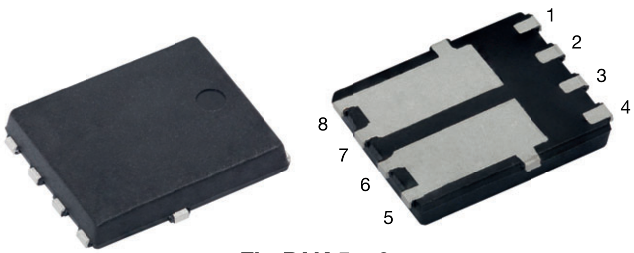
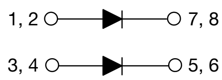
Hyper Fast Rectifier, 2 x 4 A FRED Pt®



FlatPAK 5 x 6



FEATURES

- Hyper fast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- Specific for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1 per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT
HALOGEN FREE

DESCRIPTION / APPLICATIONS

State of the art hyper fast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyper fast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

MECHANICAL DATA

Case: FlatPAK 5 x 6
Molding compound meets UL 94 V-0 flamming rating
Base P/N-M3 - halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

M3 suffix meets JESD 201 class 2 whisker test

PRODUCT SUMMARY	
Package	FlatPAK 5 x 6
$I_{F(AV)}$	2 x 4 A
V_R	200 V
V_F at I_F	0.7 V
$t_{rr\ (typ.)}$	25 ns
T_J max.	175 °C
Diode variation	Separated cathode

ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage		V_{RRM}		200	V
Average rectified forward current	per device	$I_{F(AV)}$	$T_{Solderpad}$ = 170 °C, DC	8	A
			$T_{Solderpad}$ = 169 °C, D = 0.5		
Non-repetitive peak surge current	per device	I_{FSM}	T_J = 25 °C, 10 ms sinusoidal pulse	173	
	per diode			87	
Operating junction and storage temperatures		T_J, T_{Stg}		-55 to +175	°C

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Breakdown voltage, blocking voltage	V_{BR}, V_R	I_R = 100 μA	200	-	-	V
Forward voltage, per diode	V_F	I_F = 4 A	-	0.87	0.96	
		I_F = 4 A, T_J = 150 °C	-	0.7	0.78	
Reverse leakage current, per diode	I_R	V_R = V_R rated	-	-	2	μA
		T_J = 150 °C, V_R = V_R rated	-	7	80	
Junction capacitance	C_T	V_R = 200 V	-	19	-	pF

DYNAMIC RECOVERY CHARACTERISTICS (T_J = 25 °C unless otherwise specified)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNITS**
Reverse recovery time	t_{rr}	I_F = 1.0 A, dI_F/dt = 50 A/μs, V_R = 30 V		-	20	-	ns
		I_F = 0.5 A, I_R = 1 A, I_{rr} = 0.25 A		-	-	25	
		T_J = 25 °C	I_F = 4 A dI_F/dt = 200 A/μs V_R = 160 V	-	17	-	
		T_J = 125 °C		-	29	-	
Peak recovery current	I_{RRM}	T_J = 25 °C		-	2.1	-	A
		T_J = 125 °C		-	4	-	
Reverse recovery charge	Q_{rr}	T_J = 25 °C		-	18	-	nC
		T_J = 125 °C		-	60	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Maximum junction and storage temperature range	T_J, T_{Stg}		-55	-	175	°C
Thermal resistance, junction to ambient, per diode	R_{thJA} (1)(2)		-	89	103	°C/W
Thermal resistance, junction to case, per diode	R_{thJC} (3)		-	1.8	2.1	

Notes

(1) The heat generated must be less than the thermal conductivity from junction to ambient: $dP_D/dT_J < 1/ R_{thJA}$

(2) Free air, mounted or recommended copper pad area; thermal resistance R_{thJA} - junction to ambient

(3) Mounted on infinite heatsink

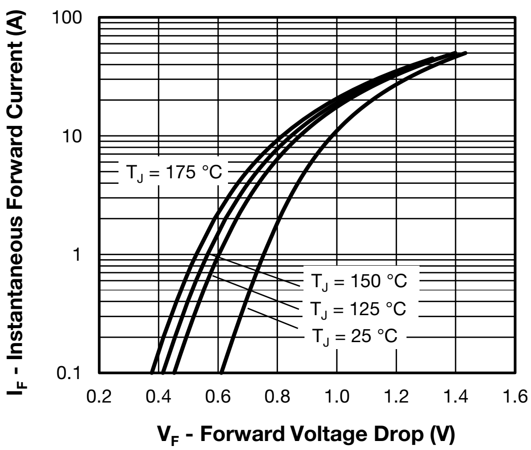


Fig. 1 - Typical Forward Voltage Drop Characteristics

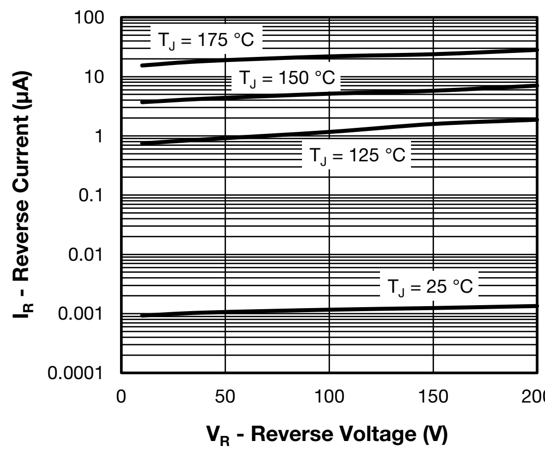


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

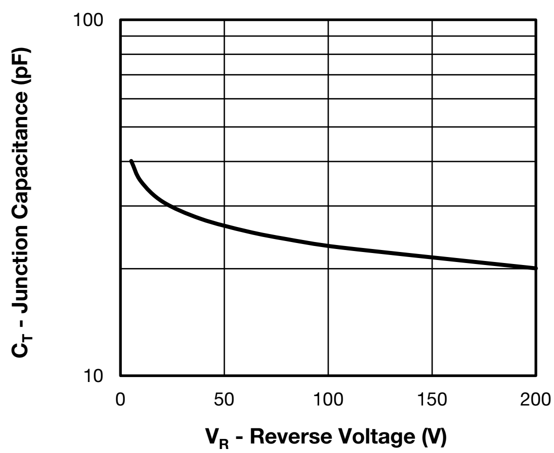


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

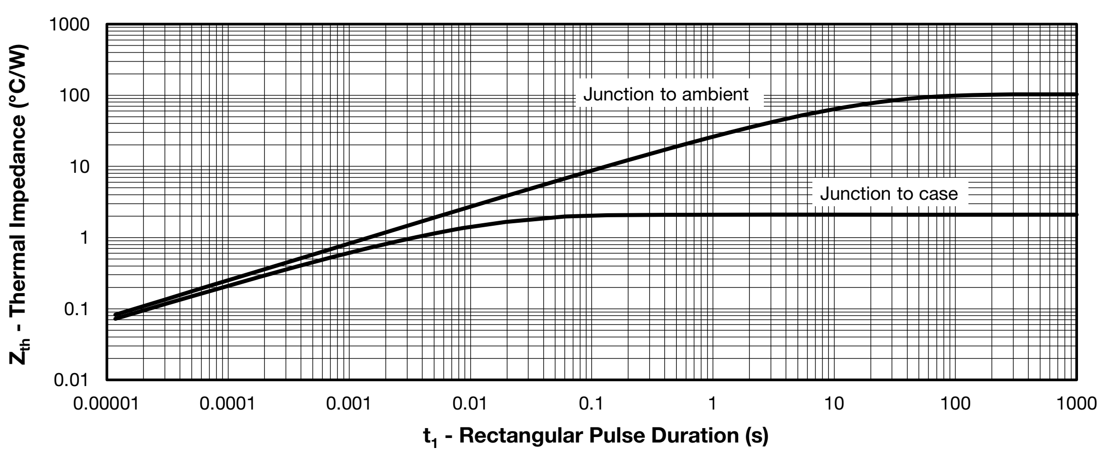


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

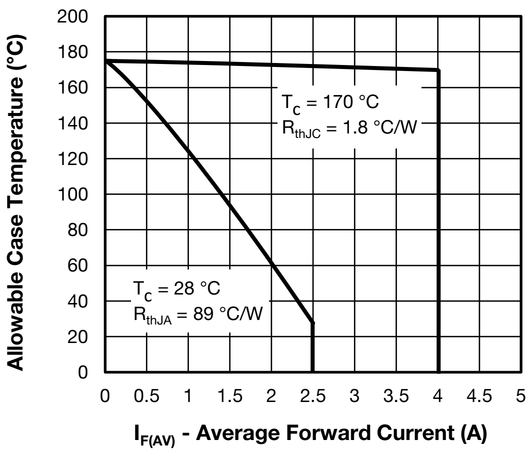


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

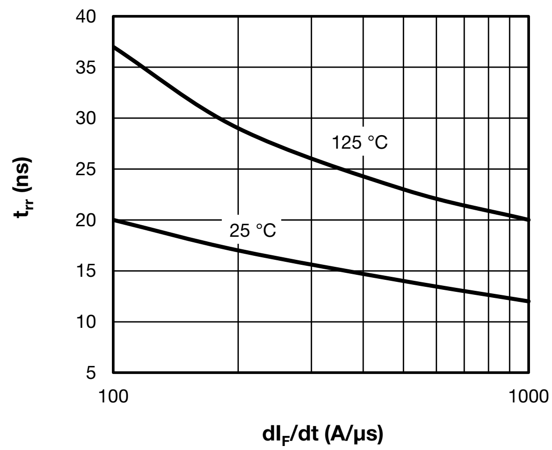


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

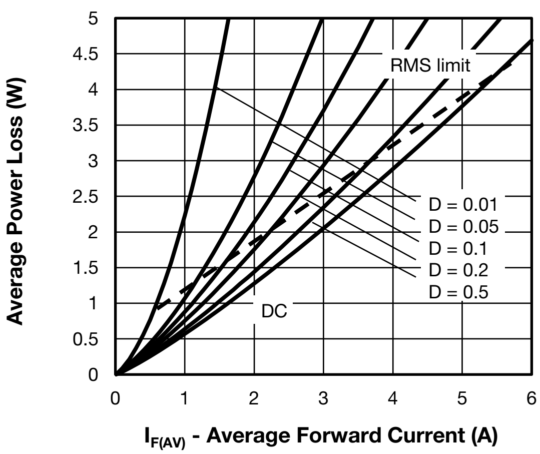


Fig. 6 - Forward Power Loss Characteristics

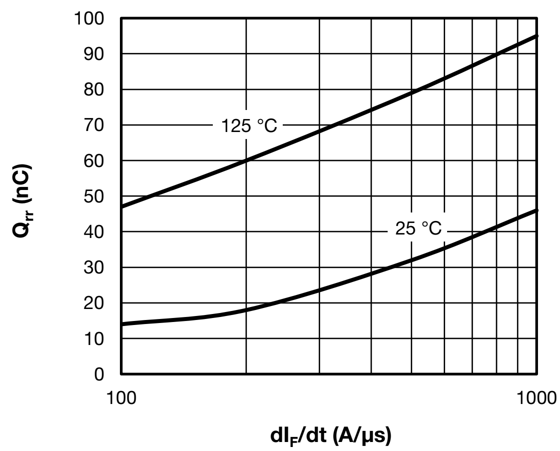
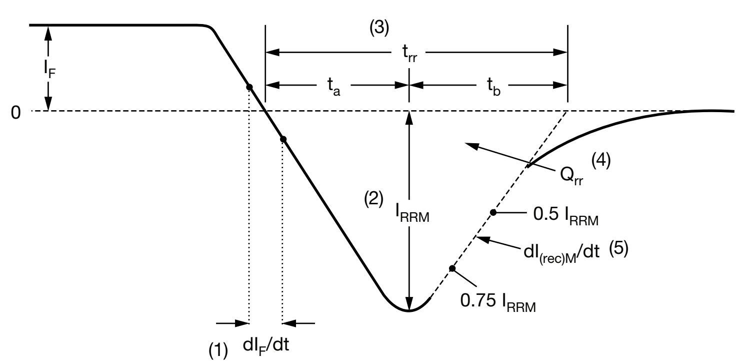


Fig. 8 - Typical Stored Charge vs. dI_F/dt



(1) dI_F/dt - rate of change of current through zero crossing

(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code	VS-	8	D	K	H	02	-M3
	1	2	3	4	5	6	7

1 - Vishay Semiconductors product

2 - Current rating (8 = 8 A)

3 - Circuit configuration:
D = separated cathode

4 - K = FlatPAK package

5 - Process type,
H = hyper fast recovery

6 - Voltage code (02 = 200 V)

8 - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (example)

PREFERRED P/N	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	PACKAGING DESCRIPTION
VS-8DKH02-M3/H	0.10	H	1500	7"diameter plastic tape and reel
VS-8DKH02-M3/I	0.10	I	6000	13"diameter plastic tape and reel

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96056
Part marking information	www.vishay.com/doc?96059
Packaging information	www.vishay.com/doc?88869

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.